ΡΛΝ	JIT
	SEMI
	CONDUCTOR

## PJQ4546P-AU

## 40V N-Channel Enhancement Mode MOSFET

Current

64 A

Voltage

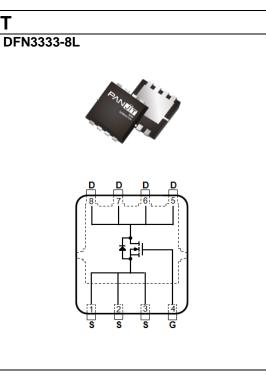
40 V

### Features

- $R_{DS(ON)}$ ,  $V_{GS}@10V$ ,  $I_D@15A < 5.6m\Omega$
- R<sub>DS(ON)</sub>, V<sub>GS</sub>@4.5V, I<sub>D</sub>@10A<7.9mΩ
- Excellent FOM
- Logic Level Drive
- AEC-Q101 qualified
- Lead free in compliance with EU RoHS 2.0
- Green molding compound as per IEC 61249 standard

### **Mechanical Data**

- Case : DFN3333-8L Package
- Terminals : Solderable per MIL-STD-750, Method 2026
- Approx. Weight : 0.03 grams



### **Maximum Ratings and Thermal Characteristics** (T<sub>A</sub>=25°C unless otherwise noted)

PARAMETE	R	SYMBOL	LIMIT	UNITS
Drain-Source Voltage		V <sub>DS</sub>	40	
Gate-Source Voltage		V <sub>GS</sub>	±20	V
Continuous Drain Current <sup>(Note 3)</sup>	Tc=25°C		64	
	Tc=100°C	I <sub>D</sub>	45	А
Pulsed Drain Current <sup>(Note 1)</sup>	T <sub>C</sub> =25°C	I <sub>DM</sub>	256	
Power Dissipation	T <sub>C</sub> =25°C	5	42	14/
	Tc=100°C	Po	21	W
Continuous Droin Current(Note 4)	T <sub>A</sub> =25 <sup>°</sup> C		15.7	
Continuous Drain Current <sup>(Note 4)</sup>	T <sub>A</sub> =70°C	I <sub>D</sub>	13.2	— A
De la Discientia a	T <sub>A</sub> =25°C	5	2.5	
Power Dissipation	T <sub>A</sub> =70°C	PD	1.8	W
Single Pulse Avalanche Energy <sup>(Note</sup>	9 5)	Eas	81	mJ
Operating Junction and Storage Te	emperature Range	T <sub>J</sub> ,T <sub>STG</sub>	-55~175	°C
Thermal Resistance <sup>(Note 4)</sup>	Junction to Case	$R_{ extsf{ heta}JC}$	3.6	°C/W
	Junction to Ambient	R <sub>θJA</sub>	60	C/W



#### Electrical Characteristics (T<sub>A</sub>=25°C unless otherwise noted)

PARAMETER	SYMBOL	TEST CONDITION	MIN.	TYP.	MAX.	UNITS
Static	•	-	•	•		-
Drain-Source Breakdown Voltage	BV <sub>DSS</sub>	V <sub>GS</sub> =0V, I <sub>D</sub> =250uA	40	-	-	V
Gate Threshold Voltage	V <sub>GS(th)</sub>	V <sub>DS</sub> =V <sub>GS</sub> , I <sub>D</sub> =50uA	1.1	1.6	2.3	
Drain-Source On-State Resistance	D	V <sub>GS</sub> =10V, I <sub>D</sub> =15A	-	4.5	5.6	
Dialit-Source Off-State Resistance	R <sub>DS(on)</sub>	V <sub>GS</sub> =4.5V, I <sub>D</sub> =10A	- 6.1 7.9		7.9	mΩ
Zero Gate Voltage Drain Current	IDSS	V <sub>DS</sub> =40V, V <sub>GS</sub> =0V	-	-	1	uA
Gate-Source Leakage Current	Igss	V <sub>GS</sub> =±20V, V <sub>DS</sub> =0V	-	-	±100	nA
Dynamic <sup>(Note 6)</sup>	1	1	1	1	1	T
Total Gate Charge	Qg		-	20	-	
Gate-Source Charge	Qgs	V <sub>DS</sub> =32V, I <sub>D</sub> =15A, V <sub>GS</sub> =10V <sup>(Note 2,3)</sup>	-	3.1	-	nC
Gate-Drain Charge	$Q_gd$	VGS=10V(Note 2,6)	-	6.4	-	
Input Capacitance	Ciss		-	1320	-	pF
Output Capacitance	Coss	V <sub>DS</sub> =25V, V <sub>GS</sub> =0V, f=1MHZ	-	250	-	
Reverse Transfer Capacitance	Crss		-	30	-	
Gate resistance	Rg	f=1MHZ	-	0.8	-	Ω
Turn-On Delay Time	td <sub>(on)</sub>		-	11	-	
Turn-On Rise Time	tr	V <sub>DS</sub> =32V, I <sub>D</sub> =15A,	-	3	-	
Turn-Off Delay Time	td <sub>(off)</sub>	V <sub>GS</sub> =10V, R <sub>G</sub> =3Ω	-	28	-	ns
Turn-Off Fall Time	tf	(1000 2,0)	-	5	-	
Drain-Source Diode						
Diode Forward Current	I <sub>S</sub>	T 0500	-	-	64	_
Pulsed Diode Forward Current	I <sub>SM</sub>	T <sub>C</sub> =25°C	-	-	256	A
Diode Forward Voltage	V <sub>SD</sub>	Is=20A, V <sub>GS</sub> =0V	-	0.85	1.3	V
Reverse Recovery Time	Trr	V <sub>GS</sub> =0V, I <sub>S</sub> =20A	-	23	-	ns
Reverse Recovery Charge	Qrr	dl <sub>S</sub> /dt=100A/us <sup>(Note 2,3)</sup>	-	15	-	nC

NOTES :

- 1. Pulse width100us, Duty cycle<2%.</td>
- 2. Essentially independent of operating temperature typical characteristics.
- 3. Chip capability with an R\_{\rm BJC}=3.6^{\circ}C/W.
- 4.  $R_{\theta JA}$  is the sum of the junction-to-case and case-to-ambient thermal resistance where the case thermal reference is defined as the solder mounting surface of the drain pins. Mounted on a 1 inch<sup>2</sup> with 2oz.square pad of copper.
- 5. The test condition is L=0.5mH,  $I_{AS}$ =18A,  $V_{DD}$ =30V,  $V_{GS}$ =10V, Starting TJ=25°C.
- 6. Guaranteed by design, not subject to production testing.

February 18,2023

0

0.2

0.4

0.6

Fig.6 Source-Drain Diode Forward Voltage

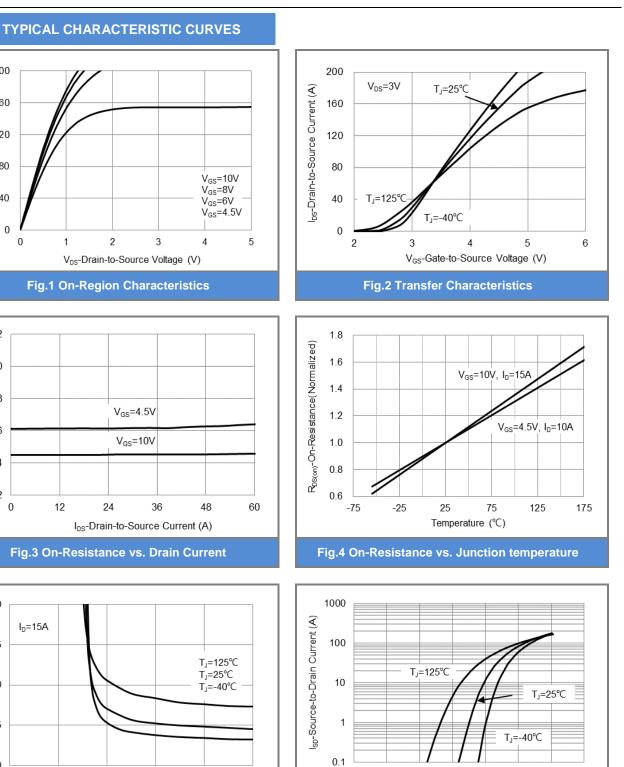
V<sub>SD</sub>-Source-to-Drain Voltage (V)

0.8

1

1.2

1.4



PJQ4546P-AU



200

160

120

80

40

0

12

8

6

4

2

20

15

10

5

0

0

2

4

Fig.5 On-Resistance Variation with V<sub>GS</sub>

6

V<sub>GS</sub>-Gate-to-Source Voltage (V)

8

10

 $R_{\text{DS(on)}}$ -On-Resistance (m $\Omega$ )

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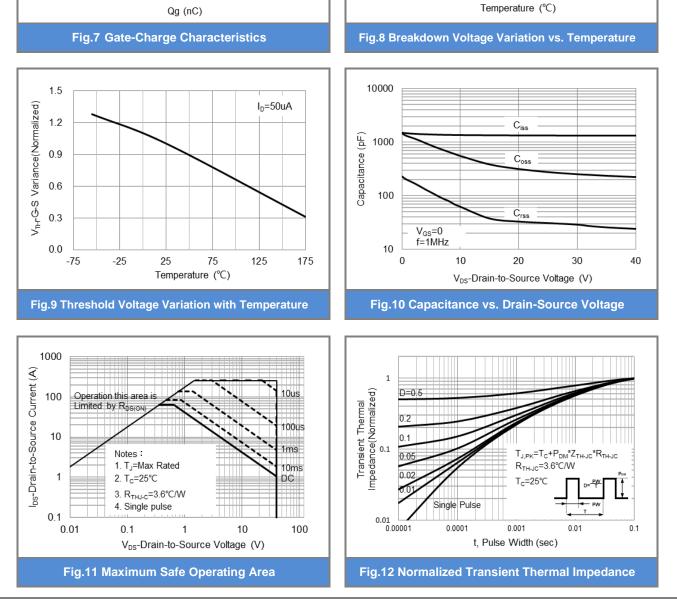
R<sub>bs(on)</sub>-On-Resistance

lps-Drain-to-Source Current (A)



February 18,2023





1.2

1.1

1.0

0.9

0.8 -75

BV<sub>DSS</sub> Variance(Normalized)

I<sub>D</sub>=250uA

-25

25

75

125

175

#### TYPICAL CHARACTERISTIC CURVES

10

15

20

25



10

8

6

4

2

0

0

5

V<sub>GS</sub>-Gate-to-Source Voltage (V)

PJQ4546P-AU

V<sub>DS</sub>=32V

I<sub>D</sub>=15A



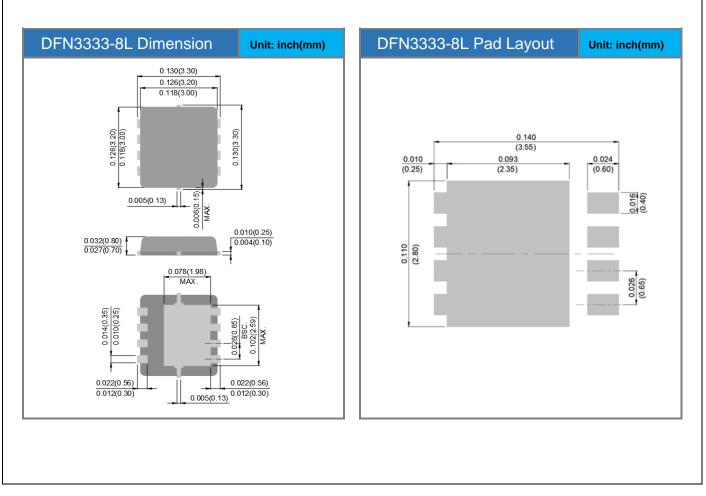


# PJQ4546P-AU

### **Product and Packing Information**

Part No.	Package Type	Packing Type	Marking
PJQ4546P-AU	DFN3333-8L	5K pcs / 13" reel	4546

### Packaging Information & Mounting Pad Layout





## PJQ4546P-AU

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